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**ENHANCED PERFORMANCE OF
BIPOLAR CASCADE LIGHT EMITTING
DIODES BY DOPING THE ALUMINUM
OXIDE APERTURES**



William J. Siskaninetz

Electron Devices Branch (AFRL/SNDD)

Aerospace Components and Subsystems Division

Sensors Directorate

Air Force Research Laboratory, Air Force Materiel Command

Wright-Patterson Air Force Base, OH 45433-7320

J.E. Ehret

Materials and Manufacturing Directorate, AFRL/ML

J.A. Lott

Air Force Institute of Technology, AFIT

J.C. Griffith and T.R. Nelson, Jr.

Sensors Directorate, AFRL/SN

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SENSORS DIRECTORATE

AIR FORCE RESEARCH LABORATORY

AIR FORCE MATERIEL COMMAND

WRIGHT-PATTERSON AIR FORCE BASE, OH 45433-7320

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/s/

WILLIAM J. SISKANINETZ
Electronics Engineer

/s/

KENICHI NAKANO
Chief, Electron Devices Branch

/s/

ROBERT T. KEMERLEY
Chief, Aerospace Components & Subsystems Division

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14. ABSTRACT Performance improvements in multiple-stage, single-cavity bipolar cascade light emitting diodes including reduced operating voltages, enhanced light generation, and reduced device heating are obtained by doping intracavity aluminum oxide apertures with silicon. This doping results in a reduced electron energy barrier and therefore a reduced series resistance which leads to better power and heating characteristics. Nearly 50% reductions in operating voltages, 200% increases in light power, and increased operating range are demonstrated. We discuss the direct implications of these results for the design of bipolar cascade vertical cavity surface emitting lasers.						
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Enhanced performance of bipolar cascade light emitting diodes by doping the aluminum oxide apertures

W. J. Siskininetz

*Sensors Directorate, Air Force Research Laboratory and
Department of Electrical and Computer Engineering,
Air Force Institute of Technology, Wright-Patterson AFB, Ohio 45433**

J. E. Ehret

*Materials and Manufacturing Directorate,
Air Force Research Laboratory, Wright-Patterson AFB, Ohio 45433*

J. A. Lott

*Department of Electrical and Computer Engineering,
Air Force Institute of Technology, Wright-Patterson AFB, Ohio 45433**

J. C. Griffith and T. R. Nelson, Jr.

Sensors Directorate, Air Force Research Laboratory, Wright-Patterson AFB, Ohio 45433

Abstract

Performance improvements in multiple-stage, single-cavity bipolar cascade light emitting diodes including reduced operating voltages, enhanced light generation, and reduced device heating are obtained by doping intracavity aluminum oxide apertures with silicon. This doping results in a reduced electron energy barrier and therefore a reduced series resistance which leads to better power and heating characteristics. Nearly 50% reductions in operating voltages, 200% increases in light power, and increased operating range are demonstrated. We discuss the direct implications of these results for the design of bipolar cascade vertical cavity surface emitting lasers.

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Single-cavity bipolar cascade (BC) vertical cavity surface emitting lasers (VCSELs) and light emitting diodes (LEDs) have shown great promise for increasing device slope and differential quantum efficiencies by epitaxially connecting in series active regions with reverse-biased tunnel junctions.^{1,2} As with conventional *p-i-n* junction VCSELs, a common design feature of the BC variety is an aluminum oxide aperture (OA) or apertures that serve to funnel the injected current toward the center of the active region for better fundamental optical mode and gain overlap. While the active region and the tunnel junction have been studied extensively and optimized to improve device performance, the only considerations typically mentioned in the literature for the OA are optimum placement at nodes of the cavity resonance, material grading, tapering, and layer thickness. However, doping of the OA within the microcavity has not been discussed to the best of the authors' knowledge. This letter discusses how doping the OAs placed inside the microcavity of single- or multiple-stage BC LEDs significantly improves overall device performance by reducing the operating voltage, increasing the light power, and reducing junction heating.

Oxide aperture layers are routinely doped when they are located within a distributed Bragg reflector (DBR) stack in *p-i-n* junction VCSEL and single-stage BC VCSEL structures.^{3,4} Generally, in single-cavity multiple-active-region BC structures undoped OAs are located within the mostly undoped (except for the degenerately doped tunnel junction layers) microcavity. The OA layers within the microcavity have been shown to reduce bistability effects due to current spreading between successive active regions.⁵ Doping the microcavity OAs will increase losses due to scattering and free-carrier absorption, however, these losses will be shown to be much less than the gains achieved by doping the OAs.

The unbiased real-space energy band diagrams of doped ($N_d = 2 \times 10^{18} \text{ cm}^{-3}$) and undoped single-stage BC VCSELs with graded OA layers at thermal equilibrium are shown in Fig. 1. Doping the graded OA layer results in a significantly reduced conduction band barrier and thus more efficient transport of injected electrons to the quantum wells (left-to-right in Fig. 1). The smaller conduction band barrier also reduces junction heating by reducing the number of confined electrons trapped behind the barrier.

Our present investigation focuses on the OA layers and we have designed our experiment around a systematic series of BC LED structures, similar to that shown in the lower panel of Fig. 1. This structure allows us to disentangle the physics of the microcavity in BC devices from the additional complications that result from laser operation in a similar BC VCSEL structure.

To investigate the electrical, optical, and electroluminescent properties of the microcavities,

BC LEDs were grown by molecular beam epitaxy in a Varian Gen II system. The BC LEDs were grown on n -type (100) GaAs substrates and consist of a microcavity designed to be in a BC VCSEL structure with one, two, three or more 2.5λ thick stages between 2000 Å thick Si doped ($N_d = 4 \times 10^{18} \text{ cm}^{-3}$) GaAs cladding layers. A single-stage device is shown schematically at the bottom of Fig. 1. Each 2.5λ thick stage consists of a graded OA located in the first node (left to right in Fig. 1), a triple quantum well active region located in the third antinode, and a tunnel junction located in the fifth node of the cavity resonance. Placing the OAs and tunnel junctions in the nodes minimizes losses and placing the quantum well in the antinode maximizes the gain achieved from the cavity. The graded OA consists of a 180 Å thick $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layer with x increasing from 0.1 to 0.9, a 300 Å thick $\text{Al}_{0.98}\text{Ga}_{0.02}\text{As}$ OA, and a 180 Å thick $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layer with x decreasing from 0.9 to 0.1. The graded OAs were Si doped with a doping concentration of $N_d \sim 2 \times 10^{18} \text{ cm}^{-3}$. The active region has three 80 Å thick $\text{In}_{0.20}\text{Ga}_{0.80}\text{As}$ quantum wells separated by 100 Å thick GaAs barriers. The GaAs tunnel junction (TJ) consists of a 200 Å thick ($N_a = 5 \times 10^{19} \text{ cm}^{-3}$) carbon doped p^{++} layer and a 200 Å thick Si -doped ($N_d \sim 2 \times 10^{19} \text{ cm}^{-3}$) n^{++} layer. Additional tunnel junction growth details appear elsewhere.⁶

The samples were processed into LEDs with square apertures and square annulus top metal contacts. The top and bottom (backside metal) ohmic contacts consist of a Ni:Ge:Au:Ni:Au metal layer profile that was annealed in a forming gas (95% Ar - 5% H_2) at 410°C for 15 seconds. Each device was dry etched using a $\text{BCl}_3\text{-Cl}_2$ recipe through the active region to form isolation mesas.

Voltage vs. current (V-I) and light power vs. current (L-I) characterization were performed using a probe station, a semiconductor parameter analyzer (SPA), and a 1 cm diameter silicon p - i - n photodetector positioned above the probes to maximize light collection across the entire current range. Since the photodetector was above the probes the collected light values are maximized relative values not absolute values. The electroluminescence (EL) characterization used the SPA as the constant current source and the output light was coupled into a silica multimode fiber (core diameter = 63 μm), aligned to maximize the collected light at 50 mA, and measured using an optical spectrum analyzer. Again, the power values are maximized relative values and not absolute values. Figure 2 shows the V-I measurements for 50 $\mu\text{m} \times 50 \mu\text{m}$ square 1-, 2-, and 3-stage BC LEDs with doped (dashed) and undoped (solid) OAs. Significant reductions in operating voltages are clearly observed for the doped OA devices, compared to the undoped OA devices. We also see nearly uniform voltage steps in going from one to three BC stages. This indicates that the 1 to 3 combinations of OA and TJ are the dominant series resistances as we would expect for good

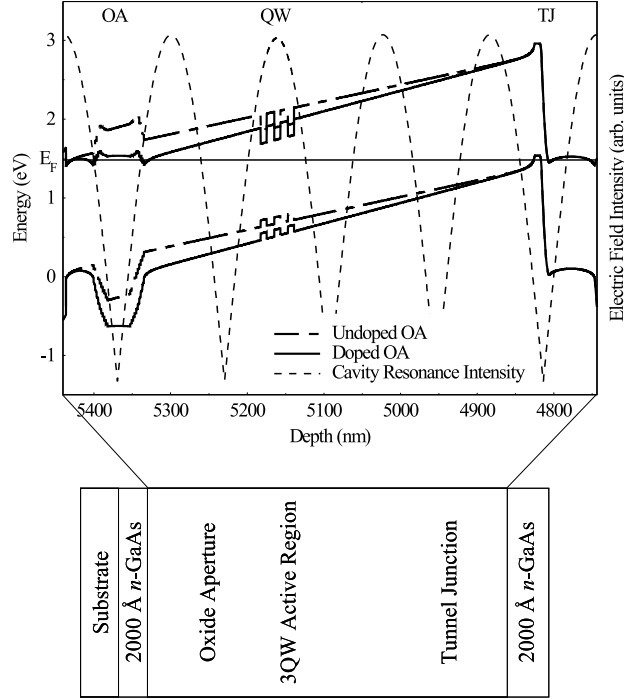


FIG. 1: Calculated electric-field intensity (dashed lines) and real-space energy band diagrams of a single-stage BC VCSEL with undoped (semi-dashed lines) and doped ($N_d = 2 \times 10^{18} \text{ cm}^{-3}$) oxide apertures (solid lines) in and around the microcavity active region (the top and bottom DBRs are not shown). Also shown is a schematic diagram of a single-stage BC LED device with the BC VCSEL microcavity.

devices. The doped OA devices demonstrate nearly a 50% reduction in operating voltage when compared to undoped OA devices with the same number of stages. The scaling between successive stages is very uniform with about 1.5 V per stage voltage for the doped graded OA structures and about 2.7 V per stage voltage for the undoped OA structures.

Figure 3 shows the L-I measurements for the same $50\mu\text{m} \times 50\mu\text{m}$ square 1-, 2-, and 3-stage BC LEDs with doped (dashed) and undoped (solid) OAs. Significant increases in light power are clearly observed with OA doping. The 2- and 3-stage devices with doped OAs have a nearly a 200% improvement in light power at 30 mA. Saturation effects are also evident in the undoped and 3-stage doped OA devices due most likely to junction heating. The L-I curves of the undoped OA devices roll over at smaller current densities due to increased junction heating as a result of the larger electron injection barrier. It is also evident that the 3-stage doped OA device is showing evidence of saturation due to junction heating implying that the power output of a BC LED with a 4th active region stage would further suffer from junction heating and thus would be less efficient.

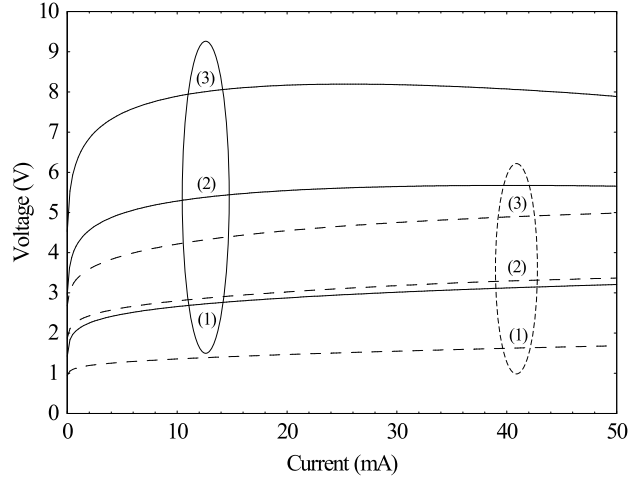


FIG. 2: Measured voltage vs. current for $50\mu\text{m} \times 50\mu\text{m}$ BC LEDs with doped (dashed lines) and undoped (solid lines) OAs. The number in parentheses indicates number of active region stages.

overall. This has been verified by growing and investigating a doped 4-stage BC LED and the L-I is less than the 3-stage device. Table I indicates the current where the onset of thermal saturation effects occurs for each device.

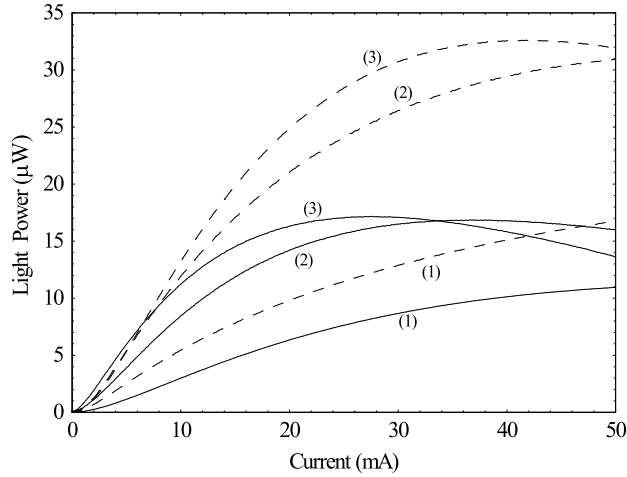


FIG. 3: Measured light output power vs. current for $50\mu\text{m} \times 50\mu\text{m}$ BC LEDs with doped (dashed lines) and undoped (solid lines) OAs. The number in parentheses indicates number of active region stages.

Figure 4 shows the EL spectra at 50 mA for the same series of BC LEDs. The undoped OA samples exhibit significantly lower quantum well luminescence and have pronounced red shifts in both the quantum well and GaAs emissions as compared to the doped OA samples. These differences are attributed to greater device heating in the undoped OA samples. These shifts are tabulated in

detail in Table I. The quantum well and GaAs peak wavelengths indicate larger red shifts per stage for the undoped OA structures ($\sim 10\text{-}20\text{ nm}$) as compared to the doped OA structures ($\sim 10\text{-}12\text{ nm}$).

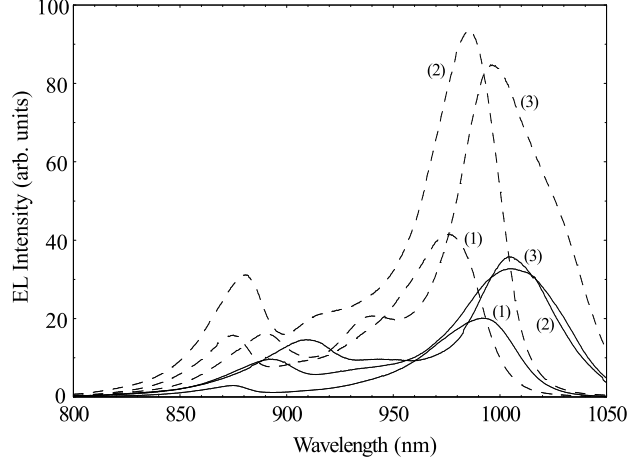


FIG. 4: Measured EL spectra at 50 mA for $50\mu\text{m} \times 50\mu\text{m}$ BC LEDs with doped (dashed lines) and undoped (solid lines) OAs. The number in parentheses indicates number of active region stages. The EL intensity is the maximum relative power collected by a silica multimode fiber and not an absolute power measurement.

TABLE I: Current at thermal rollover and EL peak wavelengths at 50 mA for doped and undoped $50\mu\text{m} \times 50\mu\text{m}$ square oxide aperture (OA) devices at room temperature.

Structure	Current at Light Peak (mA)	GaAs Peak (nm)	QW Peak (nm)
1-Stage Doped OA	$\gg 50$	874.7	976.0
2-Stage Doped OA	> 50	880.6	985.0
3-Stage Doped OA	39.4	890.9	996.5
1-Stage Undoped OA	~ 50	874.9	992.7
2-Stage Undoped OA	35.6	893.0	1004.8
3-Stage Undoped OA	26.3	909.7	1004.8

This research shows that doping the graded intracavity OAs of BC LEDs significantly improves device performance by reducing the applied voltage, increasing optical recombination, reducing the red shift due to device heating, and increasing the saturation current where thermal rollover becomes evident. This doped OA technique has immediate applications for BC VCSEL designs.

By placing doped OAs in the microcavities of VCSELs, as shown in the top panel of Fig. 1, a laser structure with significantly improved power/performance characteristics should be achieved. For VCSEL designs with intracavity contacts, the smaller series resistance should result in higher modulation frequencies in addition to the improved light output vs. power characteristics seen in the LED structures.

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* Electronic mail: william.siskaninetz@wpafb.af.mil

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